

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	249	(438/708).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/22 12:47
L2	197	(438/709).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/22 12:48
L5	1	((semiconductor adj substrate) and ((film or layer) with ((dry adj etch\$5) or ((reactive ion etching) or ("RIE")))) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint and intensit\$4 and wavelength).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/22 12:54
L6	1	((semiconductor adj substrate) and ((film or layer) with ((dry adj etch\$5) or ((reactive ion etching) or ("RIE")))) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint and intensit\$4 and wavelength).clm.	US-PGPUB	OR	ON	2006/11/22 12:54
L7	2	((film or layer) and (dry adj etch\$5) and (plasma adj (emis\$4 or discharg\$4)) and wavelength and endpoint).clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/22 12:55
L8	1	((film or layer) and (dry adj etch\$5) and (plasma adj (emis\$4 or discharg\$4)) and wavelength and endpoint).clm.	US-PGPUB	OR	ON	2006/11/22 12:55
L11	1522	(438/710).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/22 13:10
S1	1	(film or layer) with (dry adj etch\$5) with (plasma adj emis\$4) with wavelength with endpoint	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 14:28

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S2	2	(film or layer) same (dry adj etch\$5) same (plasma adj emis\$4) same wavelength same endpoint	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 14:28
S3	18	(film or layer) and (dry adj etch\$5) and (plasma adj emis\$4) and wavelength and endpoint	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:07
S4	50	(film or layer) and (dry adj etch\$5) and (plasma adj (emis\$4 or discharg\$4)) and wavelength and endpoint	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/22 12:54
S5	1	(film or layer) with (dry adj etch\$5) with (plasma adj (emis\$4 or discharg\$4)) with wavelength with endpoint	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 14:29
S6	4	(film or layer) same (dry adj etch\$5) same (plasma adj (emis\$4 or discharg\$4)) same wavelength same endpoint	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/29 14:29
S7	1763	(438/706).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/06 14:01
S8	1770	(438/706).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/10/06 14:01
S9	1	(film or layer) and (dry adj etch\$5) and (plasma adj emis\$4) and wavelength and endpoint and ("SiCN") and ("SiON")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:09

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S10	0	438/706,5.ccls. and (film or layer) and (dry adj etch\$5) and (plasma adj emis\$4) and wavelength and endpoint and ("SiCN") and ("SiON")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:10
S11	1	"438"/\$.ccls. and (film or layer) and (dry adj etch\$5) and (plasma adj emis\$4) and wavelength and endpoint and ("SiCN") and ("SiON")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:10
S12	0	"257"/\$.ccls. and (film or layer) and (dry adj etch\$5) and (plasma adj emis\$4) and wavelength and endpoint and ("SiCN") and ("SiON")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:10
S13	1	semiconductor and (film or layer) and (dry adj etch\$5) and (plasma adj emis\$4) and wavelength and endpoint and ("SiCN") and ("SiON")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:11
S14	1	semiconductor and (film or layer) and (dry adj etch\$5) and (plasma adj emis\$4) and wavelength and endpoint and (("SiCN") or ("SiON"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:11
S15	1	(film or layer) and (dry adj etch\$5) and (plasma adj emis\$4) and wavelength and endpoint and (("SiCN") or ("SiON"))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:11
S16	6	(("5668019") or ("6514375") or ("5946082") or ("5450205") or ("5362356") or ("5322590")).PN.	USPAT	OR	OFF	2005/10/12 08:55
S17	1	(film or layer) and (dry adj etch\$5) and (plasma adj (emis\$4 or discharg\$4)) and wavelength and endpoint and ("SiCN") and ("SiON")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:12

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S18	1	(film or layer) and (dry adj etch\$5) and (plasma adj (emis\$4 or discharg\$4)) and wavelength and endpoint and ("SiCN") or ("SiON")	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:22
S19	1	((("SiCN") or ("SiON")) adj (film or layer)) and (dry adj etch\$5) and (plasma adj (emis\$4 or discharg\$4)) and wavelength and endpoint	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:23
S20	915	((("SiCN") or ("SiON")) adj (film or layer)) and (dry adj etch\$5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:23
S21	19	((("SiCN") or ("SiON")) adj (film or layer)) and (dry adj etch\$5) and (plasma adj (emis\$4 or discharg\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:38
S22	13	((("SiCN") or ("SiON")) adj (film or layer)) and (dry adj etch\$5) and wavelength and endpoint	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:36
S23	1	((("SiCN") or ("SiON")) adj (film or layer)) and (dry adj etch\$5) and wavelength and endpoint and (plasma adj (emis\$4 or discharg\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:35
S24	11	((("SiCN") or ("SiON")) adj (film or layer)) and (dry adj etch\$5) and wavelength and endpoint and plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:38
S25	6	((("SiCN") or ("SiON")) adj (film or layer)) and (dry adj etch\$5) and wavelength and endpoint and plasma and (emiss\$4 or discharg\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:37

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S26	19	((("SiCN") or ("SiON")) adj (film or layer)) and (dry adj etch\$5) and (plasma adj (emis\$4 or discharg\$4)) and plasma	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/10/12 07:39
S27	2	((("SiCN") or ("SiON")) adj (film or layer)) and (dry adj etch\$5) and (plasma adj (emis\$4 or discharg\$4)) and plasma and wavelength	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/22 12:47
S28	1	((("SiCN") or ("SiON")) adj (film or layer)) and (dry adj etch\$5) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 14:24
S29	2	("5668019" or ("6703285")).PN.	USPAT	OR	OFF	2006/07/26 12:24
S30	10	(semiconductor adj substrate) and ((film or layer) with (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 14:29
S31	1	(semiconductor adj substrate) and ((film or layer) near (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 14:26
S32	26	(semiconductor adj substrate) and ((film or layer) and (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 14:26
S33	9	(semiconductor adj substrate) and ((film or layer) with (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint and intensit\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 14:37
S34	13	(semiconductor adj substrate) and ((film or layer) and (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint and intensit\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 14:30

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S35	8	(semiconductor adj substrate) and ((film or layer) with (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint and intensit\$4 and @ad<="20040129"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/30 13:28
S36	1	(semiconductor adj substrate) and ((film or layer) near (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint and intensit\$4 and @ad<="20040129"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 14:39
S37	12	(semiconductor adj substrate) and ((film or layer) and (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint and intensit\$4 and @ad<="20040129"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 14:39
S38	1	(semiconductor adj substrate) and ((film or layer) with (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint and luminous and intensit\$4 and @ad<="20040129"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 14:43
S39	3	(semiconductor adj substrate) and ((film or layer) and (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint and luminous and intensit\$4 and @ad<="20040129"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/28 14:43
S40	4	(semiconductor adj substrate) and ((film or layer) with (dry adj etch\$5)) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint and intensit\$4 and wavelength and @ad<="20040129"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/03/30 13:31
S41	39	(semiconductor adj substrate) and ((film or layer) with ((dry adj etch\$5) or ((reactive ion etching) or ("RIE")))) and (plasma adj (emis\$4 or discharg\$4)) and plasma and endpoint and intensit\$4 and wavelength and @ad<="20040129"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/22 12:54
S42	1	("6919259").PN.	USPAT	OR	OFF	2006/07/26 12:25